

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

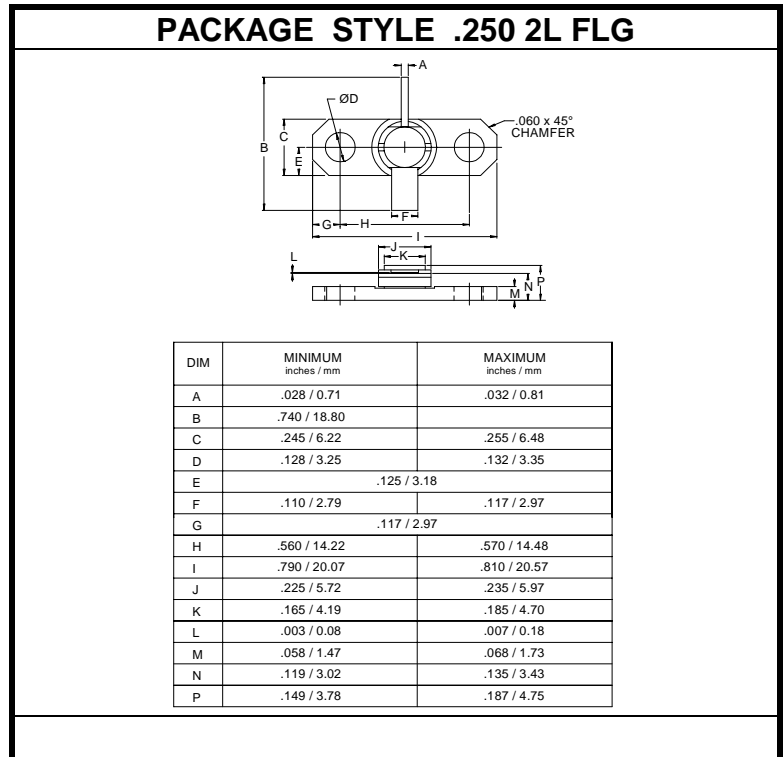
The **ASI TRW3005** is Designed for General Purpose Class C Power Amplifier Applications up to 3500 MHz.

FEATURES:

- $P_G = 4.5$ dB min. at 5 W / 3,000 MHz
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	700 mA
V_{CC}	30 V
P_{DISS}	17.6 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	8.5 °C/W


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	45			V
BV_{CER}	$I_C = 5.0$ mA $R_{BE} = 10 \Omega$	45			V
BV_{EBO}	$I_E = 10$ mA	3.5			V
I_{CBO}	$V_{CB} = 28$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	300		300	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			7.5	pF
P_G η_c	$V_{CC} = 28$ V $P_{OUT} = 5.0$ W $f = 3.0$ GHz	4.5 30			dB %